



N-CHANNEL ENHANCEMENT MODE MOSFET WITH SCHOTTKY DIODE

Features

- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low R_{DS(ON)} minimizes conduction losses
 - Low V_{SD} reducing the losses due to body diode conduction
 - Low Q_{rr} lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_g/Q_{gs}) ratio reduces risk of shootthrough or cross conduction currents at high frequencies
 - Avalanche rugged I_{AR} and E_{AR} rated
- Lead Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

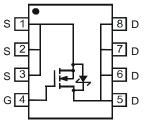
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)





Top View



Top View Internal Schematic

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 3) V _{GS} = 4.5V	Steady State	TA = 25°C TA = 85°C	I _D	10.4 6.6	А
Pulsed Drain Current (Note 4)			I _{DM}	63	Α
Avalanche Current (Notes 4 & 5)			I_{AR}	30	Α
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.1mH			E _{AR}	45	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1.55	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	R _{0JA}	81.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on 1 in * 1 in FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
- 4. Repetitive rating, pulse width limited by junction temperature.
- 5. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25$ °C.

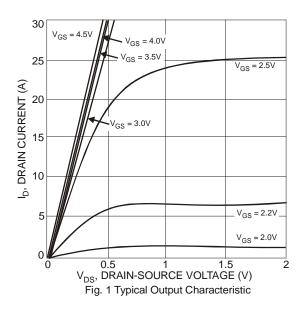


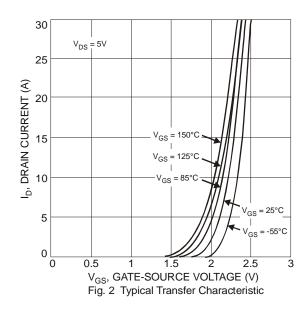
Electrical Characteristics @ T_A = 25°C unless otherwise stated

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	100	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	1.0	-	2.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	-		9	13	mΩ	$V_{GS} = 10V, I_D = 10.4A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	10	14		$V_{GS} = 4.5V, I_D = 10.4A$	
Forward Transfer Admittance	Y _{fs}	-	23	-	S	$V_{DS} = 5V, I_{D} = 10.4A$	
Diode Forward Voltage	V _{SD}	-	0.37	0.5	V	$V_{GS} = 0V, I_{S} = 1A$	
Maximum Body-Diode + Schottky Continuous Current	Is	-	-	5	Α	-	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	-	2296	-	pF	V 45V V 0V	
Output Capacitance	Coss	-	164	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	120	-	pF	1 = 1.000112	
Gate Resistance	Rg	0.26	1.3	2.34	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge V _{GS} = 4.5V	Qg	-	19.3	-	nC		
Total Gate Charge V _{GS} = 10V	Qg	-	45.7	-	nC	$V_{DS} = 15V$, $V_{GS} = 10V$, $I_{D} = 10.4A$	
Gate-Source Charge	Q _{qs}	-	5.0	-	nC		
Gate-Drain Charge	Q _{gd}	-	2.9	-	nC		
Turn-On Delay Time	t _{D(on)}	-	5.5	-	ns	$V_{GS} = 10V, V_{DS} = 15V,$ $R_{G} = 3\Omega, R_{L} = 1.2\Omega$	
Turn-On Rise Time	t _r	-	24.4	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	33.1	-	ns		
Turn-Off Fall Time	t _f	-	6.6	-	ns		

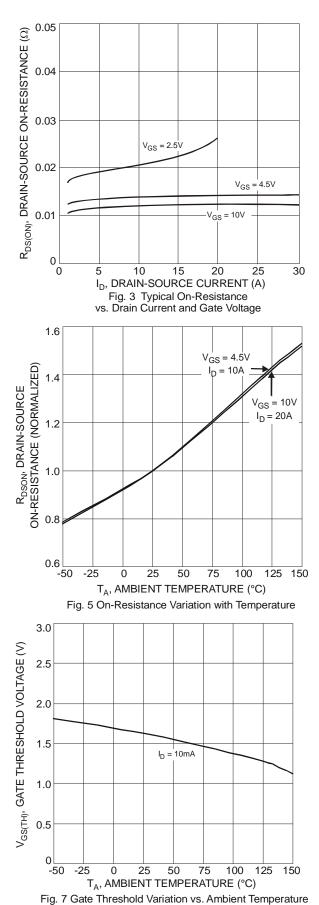
Notes:

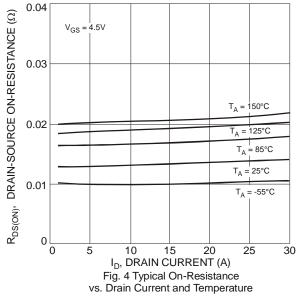
- 6. Short duration pulse test used to minimize self-heating effect. 7. Guaranteed by design. Not subject to production testing.











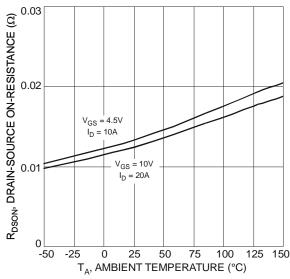


Fig. 6 On-Resistance Variation with Temperature

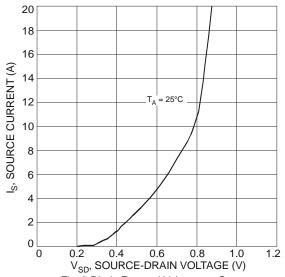
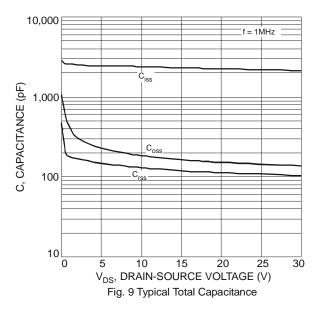
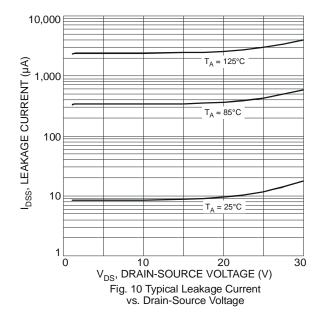


Fig. 8 Diode Forward Voltage vs. Current







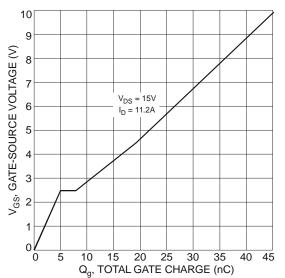


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

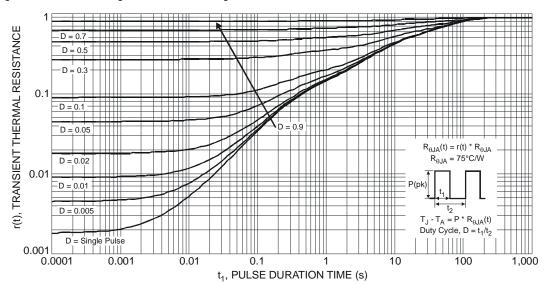


Fig. 12 Transient Thermal Response

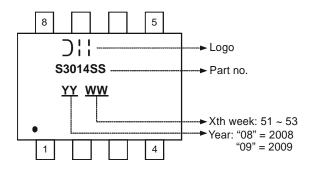


Ordering Information (Note 8)

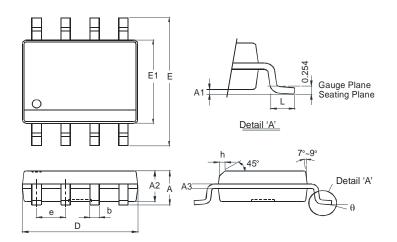
Part Number	Case	Packaging
DMS3014SSS-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

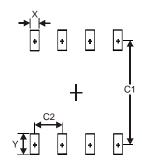


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
А3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	-	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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